

Abstract Submitted  
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**Physical properties of the wide band gap II-IV nitride MgSiN<sub>2</sub>**

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<sup>1</sup>J. B. Quirk, M. Rålander, C. M. McGilvery, R. Palgrave and M. A. Moram, Appl. Phys. Lett. 105, 112108 (2014), M. Rålander and M. A. Moram, Mater. Res. Express 3, 85902 (2016).

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